

Kookjin Lee

List of Publications by Year in descending order

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14
docs citations

14
times ranked

62
citing authors

#	ARTICLE	IF	CITATIONS
1	Understanding tunable photoresponsivity of two-dimensional multilayer phototransistors: Interplay between thickness and carrier mobility. Applied Physics Letters, 2020, 116, .	1.5	14
2	Understanding of the aging pattern in quantum dot light-emitting diodes using low-frequency noise. Nanoscale, 2020, 12, 15888-15895.	2.8	12
3	Transfer of transition-metal dichalcogenide circuits onto arbitrary substrates for flexible device applications. Nanoscale, 2019, 11, 22118-22124.	2.8	9
4	Modeling and Understanding the Compact Performance of hâ€œBN Dualâ€œGated ReS 2 Transistor. Advanced Functional Materials, 2021, 31, 2100625.	7.8	9
5	Hot-Electron-Induced Punch-Through (HEIP) Effect in p-MOSFET Enhanced by Mechanical Stress. IEEE Electron Device Letters, 2021, 42, 1424-1427.	2.2	9
6	Real-time effect of electron beam on MoS₂ field-effect transistors. Nanotechnology, 2020, 31, 455202.	1.3	8
7	Detection and Accurate Classification of Mixed Gases Using Machine Learning with Impedance Data. Advanced Theory and Simulations, 2020, 3, 2000012.	1.3	7
8	Multiple machine learning approach to characterize two-dimensional nanoelectronic devices via featurization of charge fluctuation. Npj 2D Materials and Applications, 2021, 5, .	3.9	7
9	Gate-Induced-Drain-Leakage (GIDL) in CMOS Enhanced by Mechanical Stress. IEEE Transactions on Electron Devices, 2022, 69, 2214-2217.	1.6	6
10	Cyclic Thermal Effects on Devices of Twoâ€œDimensional Layered Semiconducting Materials. Advanced Electronic Materials, 2021, 7, 2100348.	2.6	4
11	Defect spectroscopy of sidewall interfaces in gate-all-around silicon nanosheet FET. Nanotechnology, 2021, 32, 165202.	1.3	3
12	Metal-Contact Improvement in a Multilayer WSe₂ Transistor through Strong Hot Carrier Injection. ACS Applied Materials & Interfaces, 2021, 13, 2829-2835.	4.0	3
13	Deep Understanding of Electron Beam Effects on 2D Layered Semiconducting Devices Under Bias Applications. Advanced Materials Interfaces, 0, , 2102488.	1.9	1
14	Significant Enhancement of HCD and TDDB in CMOS FETs by Mechanical Stress. , 2022, , .		1